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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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Quad. 2-to-1-line Data Selectors/Multiplexers (with noninverted 3-state outputs)

RENESAS

ADE-205-478 (Z) 1st. Edition Sep. 2000

Description

The large output drive capability coupled with the 3-state feature make this device ideal for interfacing with bus lines in a bus organized system. When the output control input line is taken high, the outputs of all four multiplexers are sent into a high impedance state. When the output control line is low, the select input chooses whether the A or B input is used.

Features

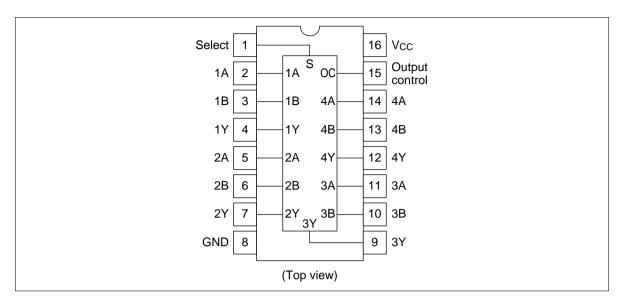
- High Speed Operation: t_{pd} (Data to Y) = 10.5 ns typ ($C_L = 50 \text{ pF}$)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: 1 µA max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max (Ta = 25°C)

Function Table

Inputs	Outputs			
Output Control	Select	Α	В	Y
L	L	L	Х	L
L	L	Н	Х	Н
L	Н	Х	L	L
L	Н	Х	Н	Н
Н	Х	Х	Х	High impedance

Notes H: high level, L: low level, X: irrelevant

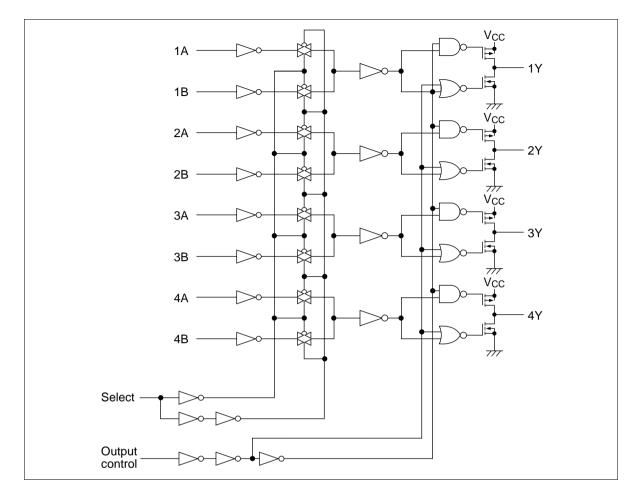
Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V _{cc}	-0.5 to +7.0	V
Input voltage	V _{IN}	–0.5 to V _{cc} + 0.5	V
Output voltage	V _{OUT}	–0.5 to V _{cc} + 0.5	V
DC current drain per pin	I _{OUT}	±35	mA
DC current drain per V_{cc} , GND	I _{CC} , I _{GND}	±75	mA
DC input diode current	Ι _{ικ}	±20	mA
DC output diode current	Ι _{οκ}	±20	mA
Power dissipation per package	P _T	500	mW
Storage temperature	Tstg	-65 to +150	°C

Logic Diagram





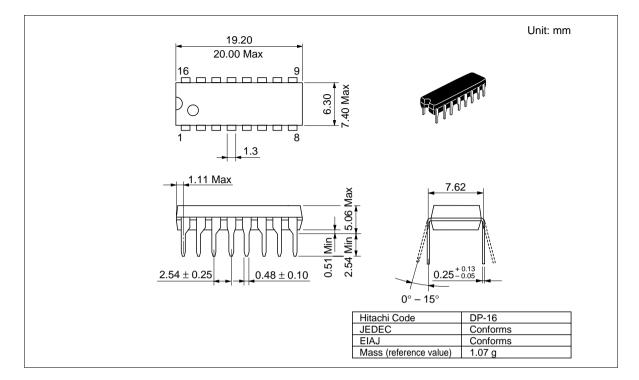
DC Characteristics

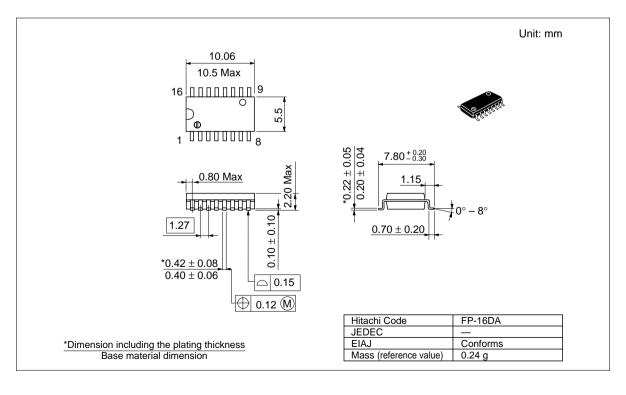
			Ta = 25°C		Ta = −40 to +85°C		_			
Item	Symbol	V_{cc} (V)	Min	Тур	Мах	Min	Max	Unit	Test Condition	าร
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15		—	3.15		_		
		6.0	4.2			4.2				
	V _{IL}	2.0	—	—	0.5		0.5	V		
		4.5	—	—	1.35	_	1.35	_		
		6.0	—	—	1.8	—	1.8			
Output voltage	$V_{\rm OH}$	2.0	1.9	2.0	—	1.9		V	$Vin = V_{\text{IH}} \text{ or } V_{\text{IL}}$	$I_{OH} = -20 \ \mu A$
		4.5	4.4	4.5	—	4.4	—	_		
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	_	_	4.13	_	_		I _{OH} = -6 mA
		6.0	5.68	_	_	5.63	_			I _{OH} = -7.8 mA
	$V_{\rm OL}$	2.0	—	0.0	0.1	—	0.1	V	$Vin = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 20 \ \mu A$
		4.5		0.0	0.1	_	0.1	_		
		6.0		0.0	0.1	—	0.1			
		4.5	_	_	0.26	_	0.33			I _{oL} = 6 mA
		6.0		—	0.26	—	0.33	_		I _{oL} = 7.8 mA
Off-state output current	I _{oz}	6.0	_	_	±0.5	_	±5.0	μA	$Vin = V_{IH} \text{ or } V_{IL},$ Vout = V _{CC} or C	
Input current	lin	6.0			±0.1		±1.0	μA	$Vin = V_{CC} \text{ or } GN$	ND
Quiescent supply current	I _{cc}	6.0	—	—	4.0	—	40	μA	Vin = V _{cc} or GN	ND, lout = 0 μ A

AC Characteristics ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

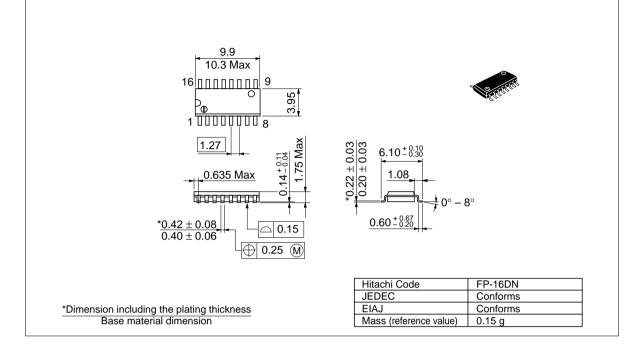
			Ta =	: 25°C	;	Ta = - +85°C			
Item	Symbol	V_{cc} (V)	Min	Тур	Мах	Min	Max	Unit	Test Conditions
Propagation delay	t _{PHL}	2.0	_	_	115	_	145	ns	Data to Y
time		4.5		11	23	—	29	-	
		6.0		—	20	—	25	-	
	t _{PLH}	2.0		—	115	—	145	ns	_
		4.5		10	23	—	29	_	
		6.0		_	20	—	25	_	
	t _{PHL}	2.0	_	_	115	_	145	ns	Select to Y
		4.5		14	23	_	29	-	
		6.0	_	_	20	_	25	-	
	t _{PLH}	2.0	_	_	115	_	145	ns	_
		4.5		14	23	_	29	-	
		6.0		_	20	_	25	-	
Output enable	t _{zL}	2.0		_	150	_	190	ns	Output control to Y
time		4.5		11	30	_	38	-	
		6.0	_	_	26	_	33	-	
	t _{zH}	2.0	_	_	150	_	190	ns	_
		4.5		13	30	_	38	-	
		6.0		_	26	_	33	-	
Output disable	t _{LZ}	2.0		_	150	_	190	ns	Output control to Y
time		4.5		14	30	_	38	-	
		6.0		—	26	_	33	-	
	t _{HZ}	2.0		_	150	_	190	ns	_
		4.5		18	30	_	38	-	
		6.0	_	_	26	_	33	-	
Output rise/fall	t _{TLH}	2.0	_	_	60	_	75	ns	
time	t_{THL}	4.5	_	4	12	_	15	-	
		6.0	_	_	10	_	13	-	
Input capacitance	Cin	—		5	10	—	10	pF	

Package Dimensions





Unit: mm



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